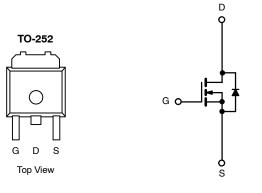
N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)		
30	0.0036 at V _{GS} = 10 V	70 ^d	67		
	0.0044 at V _{GS} = 4.5 V	70 ^d	- 07		



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET ٠
- 100 $\%~R_{q}$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC ٠

APPLICATIONS

- Power Supply
- Secondary Synchronous Rectification
- DC/DC Converter

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	v	
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	1-	70 ^d	
Continuous Drain Current (1) = 150°C)	T _C = 70 °C		60 ^d	A
Pulsed Drain Current		I _{DM}	120	A
Avalanche Current		I _{AS}	45	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	101	mJ
Maniana Diata di adi	T _C = 25 °C	Р	78.1 ^b	14/
Maximum Power Dissipation ^a	T _A = 25 °C ^c	– P _D –	3.1	W
Operating Junction and Storage Temperature Rai	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.6	0/10		

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).

d. Package limited.



HALOGEN FREE

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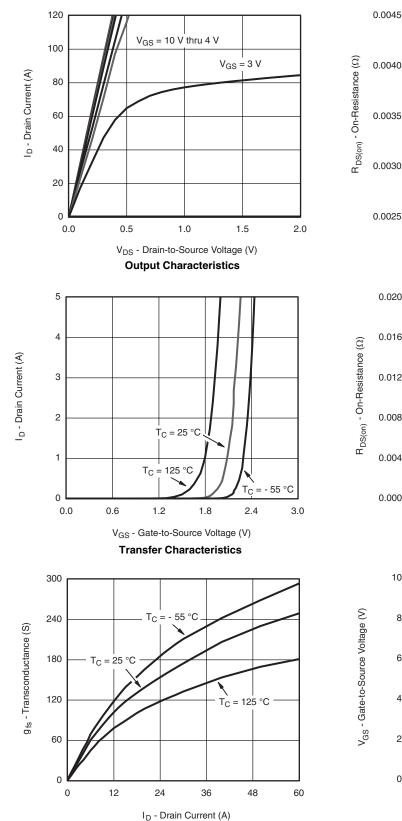
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•	•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_{D} = 250 \mu A$	30		\		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1		2.5	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			50	μΑ	
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	50			Α	
	_	V _{GS} = 10 V, I _D = 22 A		0.0030	0.0036		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0036	0.0044	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		110		S	
Dynamic ^b	•		•				
Input Capacitance	C _{iss}			3535			
Output Capacitance	C _{oss}	$V_{GS} = 0 V$, $V_{DS} = 15 V$, f = 1 MHz		680		pF	
Reverse Transfer Capacitance	C _{rss}			400			
Total Gate Charge ^c	Qg			67	100		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		10.5		nC	
Gate-Drain Charge ^c	Q _{gd}			12.2			
Gate Resistance	Rg	f = 1 MHz	0.3	1.4	2.8	Ω	
Turn-On Delay Time ^c	t _{d(on)}			11	20		
Rise Time ^c	t _r	V_{DD} = 15 V, R_L = 1.5 Ω		10	20		
Turn-Off Delay Time ^c	t _{d(off)}	$\text{I}_\text{D}\cong$ 10 A, V_GEN = 10 V, R_g = 1 Ω		35	53	ns	
Fall Time ^c	t _f			10	20	1	
Drain-Source Body Diode Ratings a	nd Characteris	stics T _C = 25 °C ^b					
Continuous Current	۱ _S				70		
Pulsed Current	I _{SM}				120	A	
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.83	1.5	V	
Reverse Recovery Time	t _{rr}			41	62	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 10 A, dl/dt = 100 A/μs		2	3	Α	
Reverse Recovery Charge	Q _{rr}			40	60	nC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

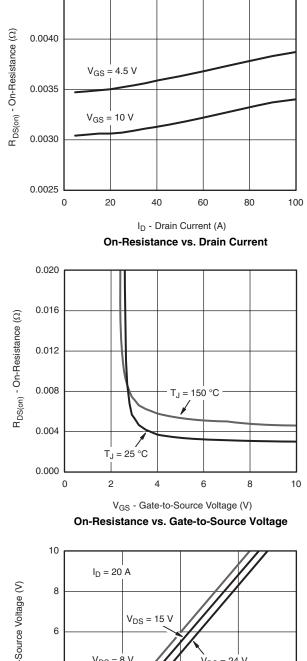
c. Independent of operating temperature.

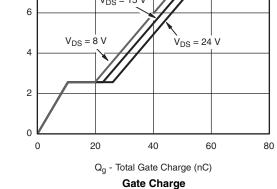
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Transconductance

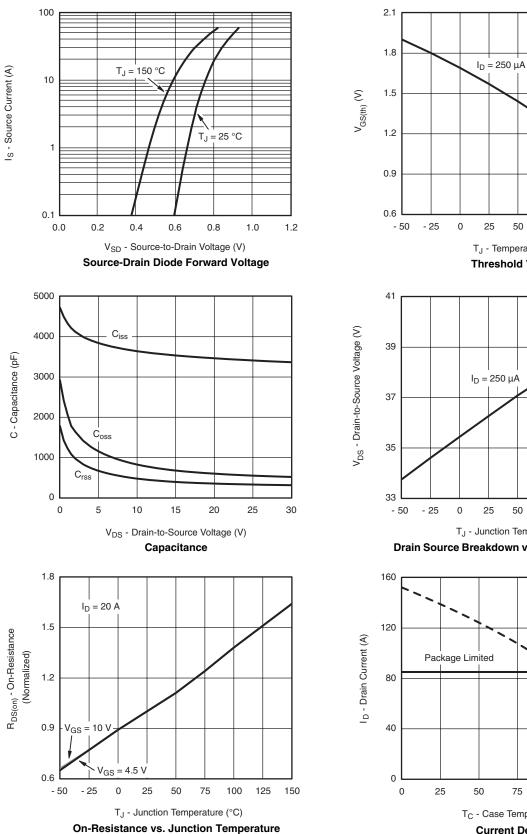
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

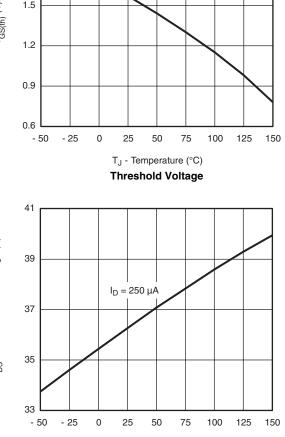




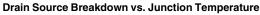
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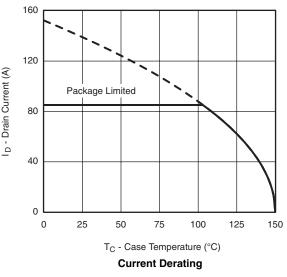
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





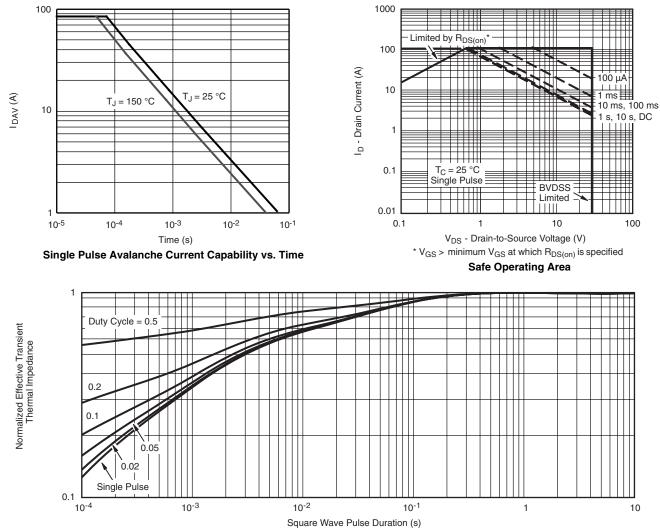
T_J - Junction Temperature (°C)





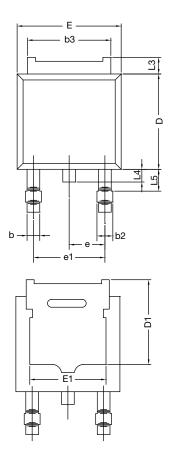
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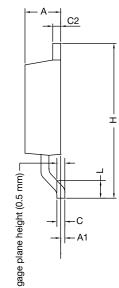
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE





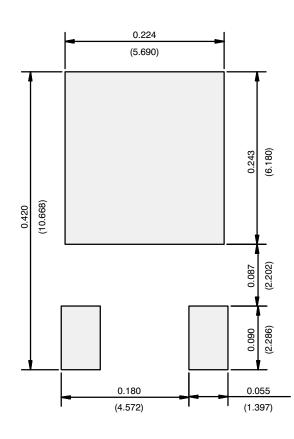
	MILLIN	IETERS	INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
А	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
Е	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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